

L9351

HIGH SIDE DRIVER

ADVANCE DATA

- LOW SATURATION VOLTAGE
- TTL COMPATIBLE INPUT
- WIDE SUPPLY VOLTAGE
- VERY LOW QUIESCENT CURRENT (30mA max)
- NO EXTERNAL COMPONENTS
- INTERNAL RECIRCULATION PATH FOR FAST DECAY OF INDUCTIVE LOAD CUR-RENT
- SHORT CIRCUIT PROTECTION
- FAILSAFE OPERATION : OUTPUT IS OFF IF THE LOGIC INPUT IS LEFT OPEN

DESCRIPTION

The L9351 is a monolithic integrated circuit designed to drive grounded resistive, inductive or mixed loads from the power supply positive side. Very low standby current (30mA max.) and internally implemented protections against load dump and reverse voltages make the device very useful in automotive applications. No external components are required because the output recirculation clamping zener is included in the chip. This zener can withstand a recirculation peak current of 550mA on a $80mH/25\Omega$ load.



The device is self-protected against overtemperature, overvoltage and overcurrent conditions. The L9351 operates over the full battery voltage range, from 4.5V (cold cranking) up to 24V (jump starting). The L9351 withstands revers battery conditions (-13V) and supply voltage transients up to 80V limiting the maximum output transistor V_{EC} to 70V by an internal zener. ON and OFF delay times of 25 μ s max in any output status, including recirculating situation, allow PWM use of L9351.

BLOCK DIAGRAM



This is advanced information on a new product now in development or undergoing evaluation. Details are subject to change without notice.

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PIN CONNECTION (top view)



Note : Pin 3 must be left open or connected to ground.

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
Vs	D.C. Supply Voltage	24	V
	D.C. Reverse Supply Voltage	–13	V
	Load Dump: 5ms ≤ trise ≤ 10ms	60	V
	Low Energy Spikes: Rsource $\ge 10\Omega$, t _{rise} = 1µs, tf = 2ms, fr Repetition Frequency = 0.2Hz	±85	V
Vi	Input Voltage	–0.3 to 7	V
lo	Output Current	Internally Limited	
P _{tot}	Total Power Dissipation at T _{case} = 90°C	17.1	W
T _j , T _{stg}	Junction and Storage Temperature	-55 to 150	°C

THERMAL DATA

Symbol	Parameter	Value	Unit	
R _{th j-amb}	Thermal Resistance Junction-ambient	Max.	80	°C/W
R _{th j} -case	Thermal Resistance Junction-case	Max.	3.5	°C/W



ELECTRICAL CHARACTERISTICS

 $(V_S = 14.4V, -40^{\circ}C \le Tj \le +125^{\circ}C$ unless otherwise specified).

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Vs	Operating Supply Voltage		4.5		24	V
VIH	Input Voltage High	4.5 < V _S < 24	2.0			V
VIL	Input Voltage Low			1	0.8	V
Ц	Input Current $0.8 < V_1 < 5.5V$				40	μA
I _{PL}	Output Leakage Current				140	μΑ
V _{sat}	Output Saturation Voltage	$I_{\rm O} = 125 \text{mAV}_{\rm S} = 4.5 \text{V}$			0.5	V
		$I_0 = 225 \text{mAV}_S = 14.4 \text{V}$			0.5	V
		$I_0 = 550 \text{mAV}_S = 14.4 \text{V}$			0.7	V
Isc	Output Short Circuit Current		0.6	1.5		А
lq	Quiescent Current	$V_{l} > 2V$			30	mA
		V _I < 0.8V Stand-by Condition		100	150	μA
V _{ZO}	Negative Output Zener Voltage	$R_L = 25\Omega$ L = 80mH on V _I Transition from "1" to "0"	- 36	- 30	- 24	V
Ton	Turn ON Delay	Resistive Load $R_L = 25\Omega$,			20	μs
T _{off}	Turn OFF Delay	$T_{j} = 25^{\circ}C$ (fig.2)			25	μs

Figure 1 : Typical Automotive Application Circuit.



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Figure 3 : Inductive Load.





DIM	mm			inch			
DIM.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
Α			4.8			0.189	
С			1.37			0.054	
D	2.4		2.8	0.094		0.110	
D1	1.2		1.35	0.047		0.053	
E	0.35		0.55	0.014		0.022	
F	0.8		1.05	0.031		0.041	
F1	1		1.4	0.039		0.055	
G		3.4		0.126	0.134	0.142	
G1		6.8		0.260	0.268	0.276	
H2			10.4			0.409	
H3	10.05		10.4	0.396		0.409	
L		17.85			0.703		
L1		15.75			0.620		
L2		21.4			0.843		
L3		22.5			0.886		
L5	2.6		3	0.102		0.118	
L6	15.1		15.8	0.594		0.622	
L7	6		6.6	0.236		0.260	
М		4.5			0.177		
M1		4			0.157		
Dia	3.65		3.85	0.144		0.152	

PENTAWATT PACKAGE MECHANICAL DATA





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